



DONGGUAN NANJING ELECTRONICS LTD., TO-126 Plastic-Encapsulate Transistors

MJE13003 TRANSISTOR (NPN)

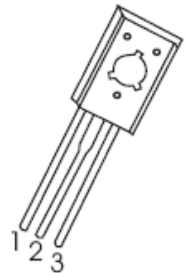
FEATURES

- Power Switching Applications

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	100	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

TO-126



1. BASE
2. COLLECTOR
3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=600\text{V}, I_E=0$			100	μA
Collector cut-off current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			10	μA
DC current gain	$h_{FE(1)*}$	$V_{CE}=10\text{V}, I_C=200\text{mA}$	9		40	
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=250\mu\text{A}$	5			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=200\text{mA}, I_B=40\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			1.1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=1\text{MHz}$	5			MHz
Fall time	t_f	$I_C=100\text{mA}$			0.5	μs
Storage time	t_s^*	$I_C=100\text{mA}$	2		4	

CLASSIFICATION of $h_{FE(1)}$

Range	9-15	15-20	20-25	25-30	30-35	35-40
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CLASSIFICATION of t_s

Rank	A1	A2	B1	B2
Range	2-2.5	2.5-3	3-3.5	3.5-4